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Xin Ouyang, Songping Wu, Zhuolin Wang, Yunhao Liu

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Synthesis and Microwave Dielectric Properties of 2ZnO·3B₂O₃-doped ZnAl₂O₄ Low-Permittivity Ceramics

Xin Ouyang^a, Songping Wu^a,*, Zhuolin Wang^a, Yunhao Liu^a

^aSchool of Chemistry and Chemical Engineering, South China University of Technology, Guangzhou, 510641, China.

ABSTRACT: $2ZnO\cdot 3B_2O_3$ -doped $ZnAl_2O_4$ ceramics were synthesized via solid-state method. Influence of different $2ZnO\cdot 3B_2O_3$ additions on the microstructure, sintering behavior and microwave dielectric properties has been investigated. The results showed that zinc borate could effectively improve the densification and expand the sintering temperature range. Microwave dielectric properties of $2ZnO\cdot 3B_2O_3$ -doped $ZnAl_2O_4$ ceramics were exhibited as follow: $\epsilon_r=8.32$, $Q\times f=93$, 600 GHz (at 14.0 GHz) and $\tau_f=-68.5$ ppm/°C. Spinel-structured zinc borate-doped $ZnAl_2O_4$ ceramics possessed comparatively low sintering temperatures, wide temperature regions (about 100°C), simultaneously, high $Q\times f$ and stable τ_f values. These outstanding performance make them promising candidate materials for millimeter-wave devices at high frequency.

Keywords: Dielectric properties; ZnAl₂O₄ ceramics; Zinc borate; Sintering aid.

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